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13. (Amended) The semiconductor device in accordance with Claim 12, wherein the semiconductor device is an insulated gate bipolar transistor, wherein the impurity region is a source region, and wherein the region irradiated is a positive-negative, junction where a parasitic diode is generated.

14. (Amended) The semiconductor device in accordance with Claim 12, wherein the semiconductor device is a metal oxide semiconductor field effect transistor, wherein the impurity region is a source region, and wherein the region irradiated is a positive-negative junction region where a parasitic diode is generated.